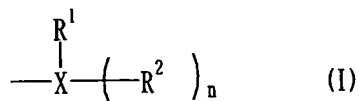


## Claims

1. A material for chemical vapor deposition comprising a precursor composed of a metal compound, wherein the material contains 100 or less particles having a size of 0.5  $\mu\text{m}$  or more in 1 ml, in particle measurement by a light scattering type submerged particle detector in a liquid phase.
- 2 The material for chemical vapor deposition according to claim 1, wherein the number of particles having a size of 0.3  $\mu\text{m}$  or more is 100 or less in 1 ml, in particle measurement by a light scattering type submerged particle detector.
3. The material for chemical vapor deposition according to claim 1 or 2, wherein the number of particles having a size of 0.2  $\mu\text{m}$  or more is 1000 or less in 1 ml, in particle measurement by a light scattering type submerged particle detector.
4. The material for chemical vapor deposition according to claim 3, wherein the number of particles having a size of 0.2  $\mu\text{m}$  or more is 100 or less in 1 ml, in particle measurement by a light scattering type submerged particle detector.
5. The material for chemical vapor deposition according to any one of claims 1 to 4, wherein the precursor is composed of a metal compound having a structure wherein the group represented by general formula (I) shown below bonds to the metal atom:



wherein X represents an oxygen atom or a nitrogen atom; n represents 0 when X is an oxygen atom or n represents 1 when X is a nitrogen atom;  $\text{R}^1$  represents an organic group having 1 to 10 carbon atoms; and  $\text{R}^2$  represents a hydrogen atom or an organic group having 1 to 10 carbon atoms.

6. The material for chemical vapor deposition according to any one of claims 1 to 4, wherein the precursor is composed of a metal compound having a structure wherein the group represented by general formula (II) shown below bonds to the metal atom:



wherein R<sup>3</sup> represents an alkyl group having 1 to 8 carbon atoms or a cyclopentadienyl group having 1 to 10 carbon atoms.

7. The material for chemical vapor deposition according to any one of claims 1 to 6, wherein the metal compound is selected from an aluminum compound, a titanium compound, a zirconium compound, a hafnium compound, a tantalum compound, and a niobium compound.

8. The material for chemical vapor deposition according to claim 7, wherein the metal compound is a hafnium compound.

9. The material for chemical vapor deposition according to any one of claims 1 to 8, which is delivered or fed in a liquid phase.

10. A method for forming metal-containing thin films by chemical vapor deposition process using the material for chemical vapor deposition according to any one of claims 1 to 9.